

LOCALIZED ANNEAL

ABSTRACT

A method of forming a device is presented. The method includes providing a wafer having an active surface and dividing the wafer into a plurality of portions. The wafer is selectively processed by localized heating of a first of the plurality of portions. The wafer is then repeatedly selectively processed by localized heating of a next of the plurality of portions until all plurality of portions have been selectively processed.

Fig. 7